

Amendments to the Specification

Please amend the paragraph beginning on line 19 of page 8 as follows:

D' Conductive material is formed within trench 30 to form at least a portion of the local interconnect being formed. Fig. 7 illustrates but one exemplary embodiment wherein a first conductive material 40 is formed, preferably by depositing, to within trench 30 to form a conductive lining therewithin. In one preferred embodiment, layer 40 is formed of an oxidation resistant material. Exemplary materials include tungsten silicide and nitrogen-rich titanium nitride. In such preferred embodiment, such thereby forms an oxidation resistant lining within line trench 30. In an alternate considered embodiment, the oxidation resistant liner material might be insulative as opposed to conductive. An exemplary insulative oxidation resistant liner material is silicon nitride. A second conductive material 42, different from first conductive material 40, is deposited to within line trench 30 on (in contact with) conductive lining 40. Exemplary materials for layer 42 include tungsten and doped polysilicon. Of course, a ~~singe~~ single conductive material could be utilized or more than two conductive materials utilized.